Abstracts

L- and S-Band 50-Watt Power GaAs MESFETs

H. Ishimura, M. Murayama, K. Arai, Y. Saito, Y. Oda and H. Kuroda. "L- and S-Band 50-Watt Power GaAs MESFETs." 1996 MTT-S International Microwave Symposium Digest 96.2 (1996 Vol. II [MWSYM]): 539-542.

L- and S-band high power GaAs FETs have been developed. At 1.8 GHz, the FET delivers an output power at 1 dB gain-compression point of 42.7W (46.3 dBm) with 13.3 dB gain and 42 % power-added efficiency, and a saturated output power of 51.3W (47.1 dBm). The developed FETs will contribute to improve the performance of microwave SSPAs used in various radar and communication systems which require higher output power and low distortion.

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